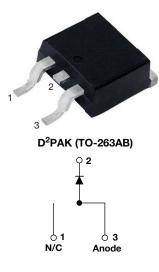
VS-HFA06TB120S-M3

Vishay Semiconductors

HEXFRED[®] Ultrafast Soft Recovery Diode, 6 A



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PRIMARY CHARACTERISTICS						
I _{F(AV)} 6 A						
V _R	1200 V					
V _F at I _F	2.4 V					
t _{rr} (typ.)	26 ns					
T _J max.	150 °C					
Package	D ² PAK (TO-263AB)					
Circuit configuration	Single					

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- · Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum peak of 245 °C
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA06TB120S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 6 A continuous current, the VS-HFA06TB120S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{BBM}) and does not exhibit any tendency to "snap-off" during the tb portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA06TB120S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS			
Cathode to anode voltage	V _R		1200	V			
Maximum continuous forward current	IF	T _C = 100 °C	6				
Single pulse forward current	I _{FSM}		80	А			
Maximum repetitive forward current	I _{FRM}		24				
Maximum neuror discinction	P _D	T _C = 25 °C	62.5	- w			
Maximum power dissipation		T _C = 100 °C	25				
Operating junction and storage temperature range	T _J , T _{Stg}		-55 to +150	°C			



COMPLIANT

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ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Cathode to anode V _{BR}		I _R = 100 μA	1200	-	-			
Maximum forward voltage		$I_{F} = 6.0 \text{ A}$	-	2.7	3.0	v		
	V _{FM}	I _F = 12 A	-	3.5	3.9			
		I _F = 6.0 A, T _J = 125 °C	-	2.4	2.8			
Maximum reverse		V _R = V _R rated	-	0.26	5.0			
leakage current	I _{RM}	T_J = 125 °C, V_R = 0.8 x V_R rated	-	110	500	μA		
Junction capacitance	CT	V _R = 200 V	-	9.0	14	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH		

DYNAMIC RECOVERY CHARACTERISTICS ($T_J = 25 \text{ °C}$ unless otherwise specified)								
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS	
	t _{rr}	I _F = 1.0 A, dI _F /dt = 200	A/ μ s, V _R = 30 V	-	26	-	ns	
Reverse recovery time	t _{rr1}	T _J = 25 °C		-	53	80		
	t _{rr2}	T _J = 125 °C	I _F = 6.0 A dI _F /dt = 200 A/μs V _R = 200 V	-	87	130		
Peak recovery current	I _{RRM1}	T _J = 25 °C		-	4.4	8.0	- A nC - A/μs	
reak recovery current	I _{RRM2}	T _J = 125 °C		-	5.0	9.0		
	Q _{rr1}	T _J = 25 °C		-	116	320		
Reverse recovery charge Peak rate of recovery current during t _b	Q _{rr2}	T _J = 125 °C		-	233	585		
	dl _{(rec)M} /dt1	T _J = 25 °C		-	180	-		
	dl _{(rec)M} /dt2	T _J = 125 °C		-	100	-		

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C		
Thermal resistance, junction to case	R _{thJC}		-	-	2.0			
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	80	K/W		
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth, and greased	-	0.5	-			
Weight			-	2.0	-	g		
weight			-	0.07	-	oz.		
Marking device		Case style D ² PAK (TO-263AB)		HFA06	TB120S			

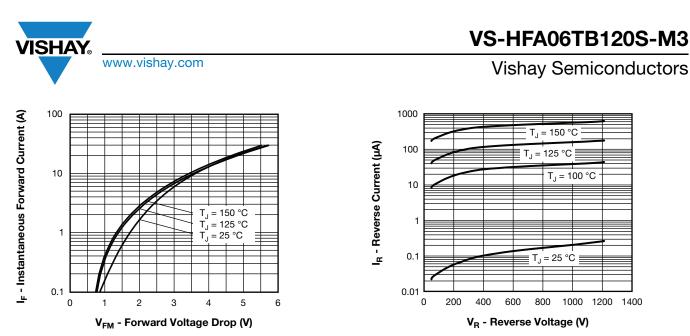


Fig. 1 - Typical Forward Voltage Drop Characteristics



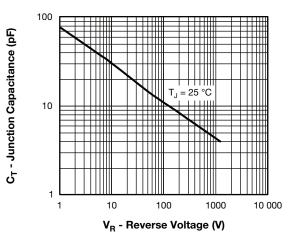


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

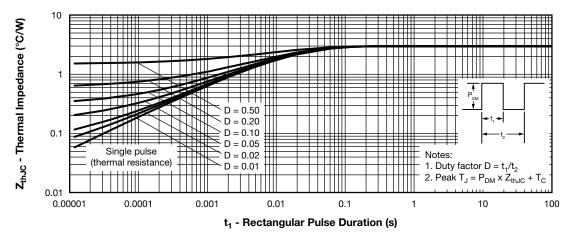


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

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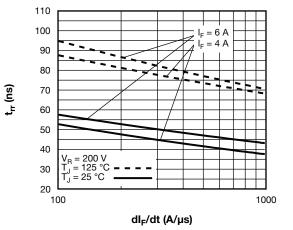


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

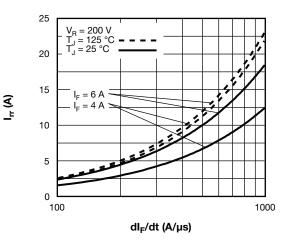


Fig. 6 - Typical Recovery Current vs. dl_F/dt

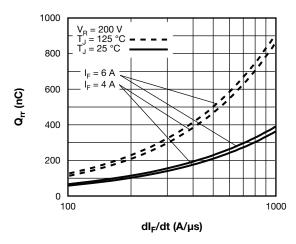


Fig. 7 - Typical Stored Charge vs. dl_F/dt

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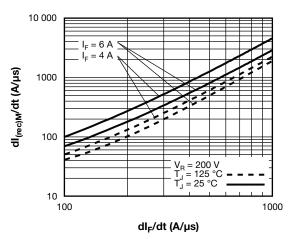


Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt

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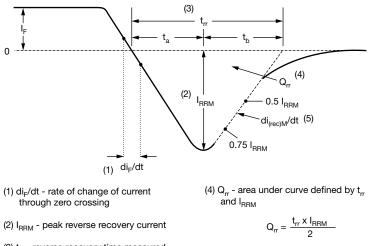
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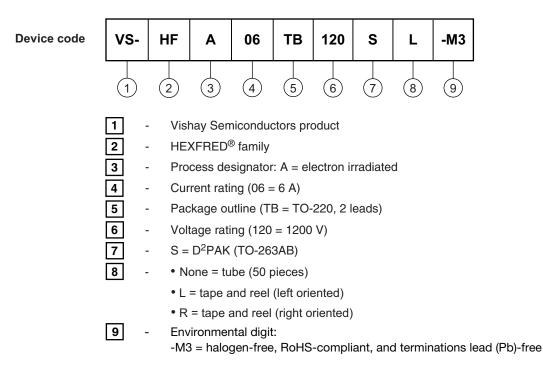


(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(5) di_{(rec)M}/dt - peak rate of change of current during t_b portion of t_{rr}

Fig. 9 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE



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VS-HFA06TB120S-M3

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ORDERING INFORMATION (Example)								
PREFERRED P/N	BASE QUANTITY	PACKAGING DESCRIPTION						
VS-HFA06TB120S-M3	50	Antistatic plastic tube						
VS-HFA06TB120SR-M3	800	13" diameter reel						
VS-HFA06TB120SL-M3	800	13" diameter reel						

LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?96164				
Part marking information	www.vishay.com/doc?95444				
Packaging information	www.vishay.com/doc?96424				

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D²PAK

DIMENSIONS in millimeters and inches



ota	ted	90	°C
<u>S</u>	cale	<u>ə:</u> 8	:1

SYMBOL	MILLIM	ETERS	INC	HES	NOTES	
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES	
Α	4.06	4.83	0.160	0.190		
A1	0.00	0.254	0.000	0.010		
b	0.51	0.99	0.020	0.039		
b1	0.51	0.89	0.020	0.035	4	
b2	1.14	1.78	0.045	0.070		
b3	1.14	1.73	0.045	0.068	4	
с	0.38	0.74	0.015	0.029		
c1	0.38	0.58	0.015	0.023	4	
c2	1.14	1.65	0.045	0.065		
D	8.51	9.65	0.335	0.380	2	

SYMBOL	MILLIM	MILLIMETERS		INCHES		
STNDUL	MIN.	MAX.	MIN.	MAX.	NOTES	
D1	6.86	8.00	0.270	0.315	3	
E	9.65	10.67	0.380	0.420	2, 3	
E1	7.90	8.80	0.311	0.346	3	
е	2.54 BSC		0.100 BSC			
Н	14.61	15.88	0.575	0.625		
L	1.78	2.79	0.070	0.110		
L1	-	1.65	-	0.066	3	
L2	1.27	1.78	0.050	0.070		
L3	0.25 BSC		0.010	BSC		
L4	4.78	5.28	0.188	0.208		

Notes

⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5 M-1994

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

(3) Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Datum A and B to be determined at datum plane H

(6) Controlling dimension: inches

⁽⁷⁾ Outline conforms to JEDEC[®] outline TO-263AB

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